PRODUCT NAME : 2N4123 NPN General Purpose Transistor (Pack of 5)

PRICE : Rs 20.00
SKU : RM2055

DESCRIPTION

Features

- Collector-Emitter Volt (Vceo): 30V
- Collector-Base Volt (Vcbo): 40V
- Collector Current (Ic): 0.2A
- hfe: 50-150 @ 2mA
- Power Dissipation (Ptot): 625mW
- Current-Gain-Bandwidth (ftotal): 250MHz
- Type: PNP

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SEMICONDUCTOR TECHNICAL DATA

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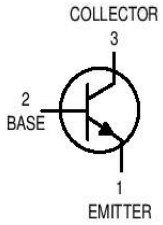
by 2N4123/D

General Purpose Transistors
NPN Silicon

2N4123
2N4124



CASE 29–04, STYLE 1
TO–92 (TO–226AA)

MAXIMUM RATINGS

Rating	Symbol	2N4123	2N4124	Unit
Collector–Emitter Voltage	V_{CEO}	30	25	Vdc
Collector–Base Voltage	V_{CBO}	40	30	Vdc
Emitter–Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	200		mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	625 5.0		mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.5 12		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage[1] (I_C = 1.0 mAdc, I_E = 0)	2N4123 2N4124	$V_{(BR)CEO}$	 30 25	 — —	Vdc
Collector–Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)	2N4123 2N4124	$V_{(BR)CBO}$	 40 30	 — —	Vdc
Emitter–Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)		$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current (V_{CB} = 20 Vdc, I_E = 0)		I_{CBO}	—	50	nAdc
Emitter Cutoff Current (V_{EB} = 3.0 Vdc, I_C = 0)		I_{EBO}	—	50	nAdc

1. Pulse Test: Pulse Width = 300 μs, Duty Cycle = 2.0%.

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2N4123 2N4124

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted) (Continued)

Characteristic		Symbol	Min	Max	Unit
ON CHARACTERISTICS					
DC Current Gain(1)		h_{FE}			—
(I_C = 2.0 mAdc, V_{CE} = 1.0 Vdc)	2N4123		50	150	
	2N4124		120	360	
(I_C = 50 mAdc, V_{CE} = 1.0 Vdc)	2N4123		25	—	
	2N4124		60	—	
Collector–Emitter Saturation Voltage(1) (I_C = 50 mAdc, I_B = 5.0 mAdc)		$V_{CE(sat)}$	—	0.3	Vdc
Base–Emitter Saturation Voltage(1) (I_C = 50 mAdc, I_B = 5.0 mAdc)		$V_{BE(sat)}$	—	0.95	Vdc
SMALL–SIGNAL CHARACTERISTICS					
Current–Gain — Bandwidth Product		f_T			MHz
(I_C = 10 mAdc, V_{CE} = 20 Vdc, f = 100 MHz)	2N4123		250	—	
	2N4124		300	—	
Input Capacitance (V_{EB} = 0.5 Vdc, I_C = 0, f = 1.0 MHz)		C_{ibo}	—	8.0	pF
Collector–Base Capacitance (I_E = 0, V_{CB} = 5.0 V, f = 1.0 MHz)		C_{cb}	—	4.0	pF
Small–Signal Current Gain		h_{fe}			—
(I_C = 2.0 mAdc, V_{CE} = 10 Vdc, R_S = 10 k ohm, f = 1.0 kHz)	2N4123		50	200	
	2N4124		120	480	
Current Gain — High Frequency		$\|h_{fe}\|$			—
(I_C = 10 mAdc, V_{CE} = 20 Vdc, f = 100 MHz)	2N4123		2.5	—	
	2N4124		3.0	—	
(I_C = 2.0 mAdc, V_{CE} = 10 V, f = 1.0 kHz)	2N4123		50	200	
(I_C = 2.0 mAdc, V_{CE} = 10 V, f = 1.0 kHz)	2N4124		120	480	
Noise Figure		NF			dB
(I_C = 100 µAdc, V_{CE} = 5.0 Vdc, R_S = 1.0 k ohm,	2N4123		—	6.0	
f = 1.0 kHz)	2N4124		—	5.0	

1. Pulse Test: Pulse Width = 300 µs, Duty Cycle = 2.0%.

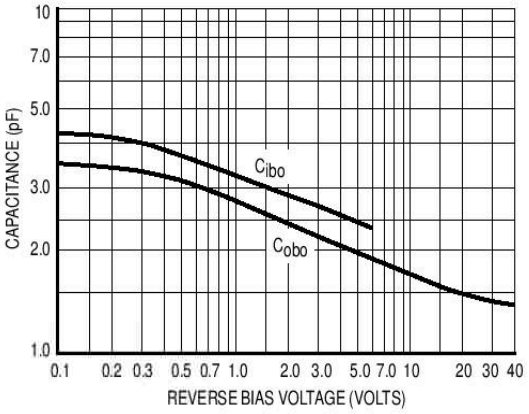

Figure 1. Capacitance

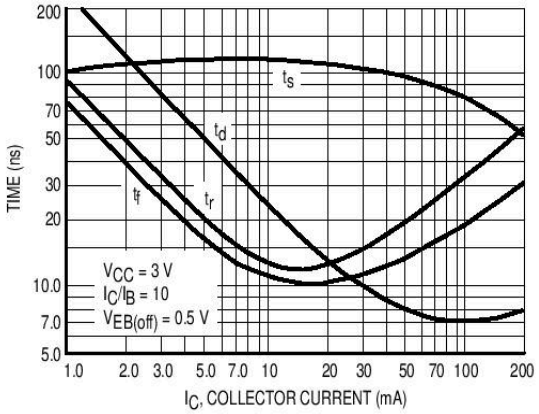

Figure 2. Switching Times